

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-11. (Canceled)
12. (Currently Amended) A silicon wafer for epitaxial growth, wherein the wafer is produced by slicing a silicon single crystal grown with doping nitrogen according to the Czochralski method (CZ method) in the region where at least the center of the wafer becomes V region in which ~~the void type~~ defects are generated and wherein the number of defects having an opening size of 20 nm or less among the void ~~type~~ defects appearing on a surface of the wafer is $0.02/\text{cm}^2$ or less.
13. (Currently Amended) The silicon wafer for epitaxial growth according to Claim 12, wherein the V region exists in the range of 80 % or more of a plane of the silicon wafer.
14. (Previously Presented) The silicon wafer for epitaxial growth according to Claim 12, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.
15. (Previously Presented) The silicon wafer for epitaxial growth according to Claim 13, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.
16. (Previously Presented) An epitaxial wafer, wherein an epitaxial layer is formed on the surface of the silicon wafer for epitaxial growth according to Claim 12.
17. (Previously Presented) An epitaxial wafer, wherein an epitaxial layer is formed on the surface of the silicon wafer for epitaxial growth according to Claim 13.
18. (Previously Presented) An epitaxial wafer, wherein an epitaxial layer is formed on the surface of the silicon wafer for epitaxial growth according to Claim 14.

19. (Previously Presented) An epitaxial wafer, wherein an epitaxial layer is formed on the surface of the silicon wafer for epitaxial growth according to Claim 15.

20. (Previously Presented) The epitaxial wafer according to Claim 16, wherein the number of stacking faults (SF) appearing on the epitaxial layer is $0.02/\text{cm}^2$ or less.

21. (Previously Presented) The epitaxial wafer according to Claim 17, wherein the number of stacking faults (SF) appearing on the epitaxial layer is $0.02/\text{cm}^2$ or less.

22. (Previously Presented) The epitaxial wafer according to Claim 18, wherein the number of stacking faults (SF) appearing on the epitaxial layer is $0.02/\text{cm}^2$ or less.

23. (Previously Presented) The epitaxial wafer according to Claim 19, wherein the number of stacking faults (SF) appearing on the epitaxial layer is $0.02/\text{cm}^2$ or less.

24. (Currently Amended) A method for producing a silicon wafer for epitaxial growth wherein a silicon wafer for epitaxial growth is produced by growing a silicon single crystal with doping nitrogen according to the CZ method, with controlling F/G ($\text{mm}^2/\text{min} \cdot \text{K}$) in the range of 0.30 or more where F (mm/min) is a rate of crystal growth and G (K/mm) is a temperature gradient near growth interface when the silicon single crystal is grown, and with controlling a passage time (min) at 1150 to 1050 °C in the range of 40 minutes or more, in the region wherein at least the center of the wafer becomes V region in which ~~the void type~~ defects are generated, and then slicing the grown silicon single crystal.

25. (Previously Presented) The method for producing a silicon wafer for epitaxial growth according to Claim 24, wherein the F/G is 0.35 or more when the silicon single crystal is grown.

26. (Currently Amended) The method for producing a silicon wafer for epitaxial growth according to Claim 24, wherein the silicon single crystal is grown so that the V region exists in the region of 80% or more of a plane of the silicon wafer.

27. (Currently Amended) The method for producing a silicon wafer for epitaxial growth according to Claim 25, wherein the silicon single crystal is grown so that the V region exists in the region of 80% or more of a plane of the silicon wafer.

28. (Previously Presented) The method for producing a silicon wafer for epitaxial growth according to Claim 24, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.

29. (Previously Presented) The method for producing a silicon wafer for epitaxial growth according to Claim 25, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.

30. (Previously Presented) The method for producing a silicon wafer for epitaxial growth according to Claim 26, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.

31. (Previously Presented) The method for producing a silicon wafer for epitaxial growth according to Claim 27, wherein a concentration of nitrogen doped in the silicon single crystal is 1×10^{13} to $1 \times 10^{14}/\text{cm}^3$.

32. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 24.

33. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 25.

34. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 26.

35. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 27.

36. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 28.

37. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 29.

38. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 30.

39. (Previously Presented) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of the silicon wafer for epitaxial growth produced by the method according to Claim 31.

40. (Currently Amended) A method for producing an epitaxial wafer by forming an epitaxial layer on a surface of a silicon wafer, comprising using a silicon wafer wherein the silicon wafer is produced by slicing a silicon single crystal grown according to the CZ method with doping nitrogen in the region where at least the center of the wafer becomes V region in which the void ~~type~~ defects are generated and wherein the number of the defects having an opening size of 20 nm or less among the void ~~type~~ defects appearing on a surface of the wafer is $0.02/\text{cm}^2$ or less.